

SIRA80DP-T1-RE3-VB Datasheet

Single-N DFN8(5X6) Trench 30V MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^{a, e}	Q _g (Typ.)
30	0.0012 at V _{GS} = 10 V	128	82 nC
	0.0015 at V _{GS} = 4.5 V	115	

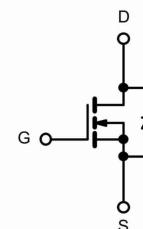
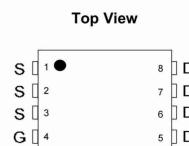
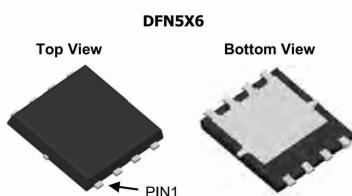
FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested



APPLICATIONS

- OR-ing
- Server



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 175 °C)	I _D	128 ^{a, e}	A
		100 ^e	
		33 ^{b, c}	
		29.8 ^{b, c}	
Pulsed Drain Current	I _{DM}	350	
Avalanche Current Pulse	I _{AS}	36	
Single Pulse Avalanche Energy	E _{AS}	64.8	mJ
Continuous Source-Drain Diode Current	I _S	90 ^{a, e}	A
		3.13 ^{b, c}	
Maximum Power Dissipation	P _D	250 ^a	W
		175	
		3.75 ^{b, c}	
		2.63 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	32	40	°C/W
Maximum Junction-to-Case	R _{thJC}	0.5	0.6	

Notes:

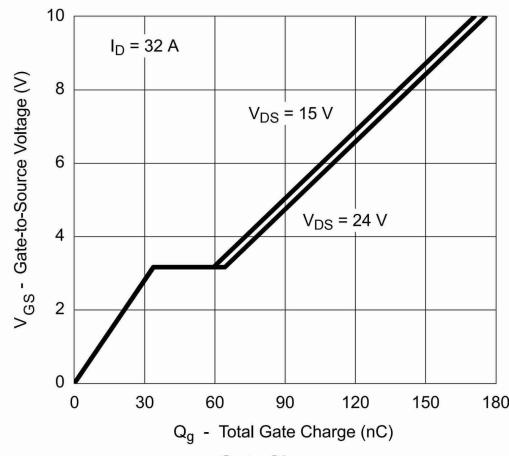
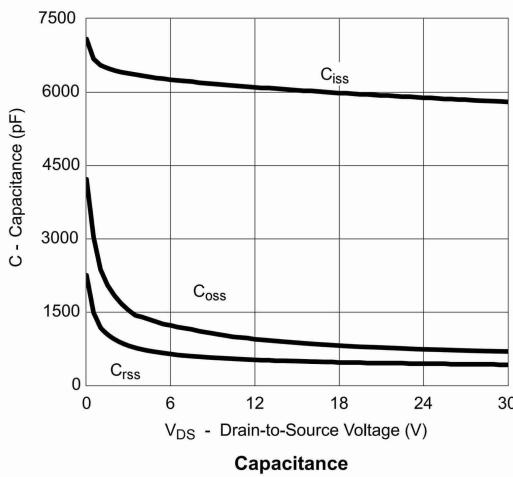
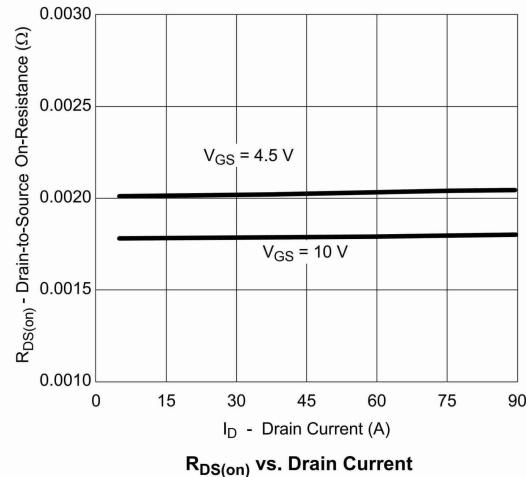
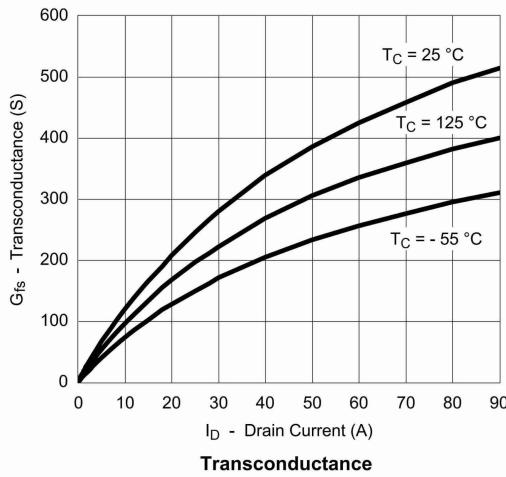
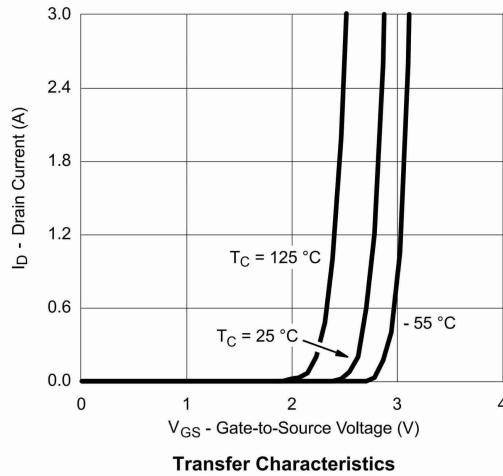
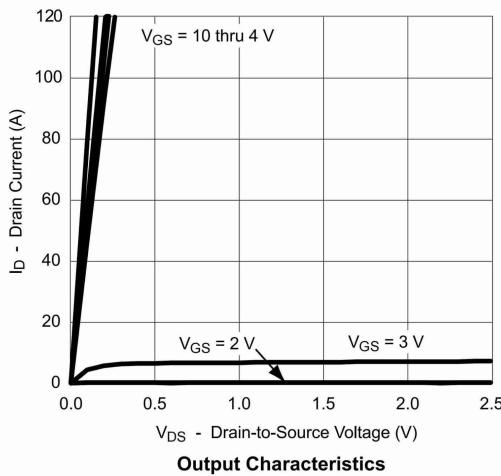
- a. Based on T_C = 25 °C.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. Maximum under steady state conditions is 90 °C/W.
- e. Calculated based on maximum junction temperature. Package limitation current is 90 A.

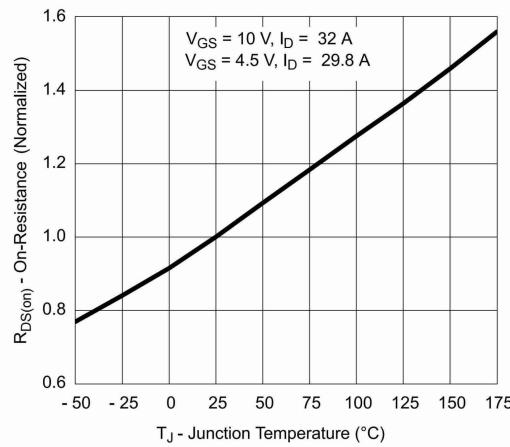
SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min .	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		35		mV/°C
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			- 7.5		
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1.5		2.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$		1		μA
		$V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 10\text{ V}$	90			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 10\text{ V}$, $I_D = 32\text{ A}$		0.0012		Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 29\text{ A}$		0.0015		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 32\text{ A}$		160		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 12.5\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		6265		pF
Output Capacitance	C_{oss}			1225		
Reverse Transfer Capacitance	C_{rss}			670		
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 32\text{ A}$		171	257	nC
				81.5	123	
Gate-Source Charge	Q_{gs}	$V_{DS} = 15\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 29\text{ A}$		34		
Gate-Drain Charge	Q_{gd}			29		
Gate Resistance	R_g	$f = 1\text{ MHz}$		1.4	2.1	Ω
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 15\text{ V}$, $R_L = 0.555\text{ }\Omega$ $I_D \geq 27\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\text{ }\Omega$		18	27	ns
Rise Time	t_r			11	17	
Turn-Off Delay Time	$t_{d(\text{off})}$			70	105	
Fall Time	t_f			10	15	
Turn-On Delay Time	$t_{d(\text{on})}$			55	83	
Rise Time	t_r	$V_{DD} = 15\text{ V}$, $R_L = 0.625\text{ }\Omega$ $I_D \geq 24\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\text{ }\Omega$		180	270	ns
Turn-Off Delay Time	$t_{d(\text{off})}$			55	83	
Fall Time	t_f			12	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$			100	A
Pulse Diode Forward Current ^a	I_{SM}				200	
Body Diode Voltage	V_{SD}	$I_S = 22\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 20\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$		52	78	ns
Body Diode Reverse Recovery Charge	Q_{rr}			70.2	105	nC
Reverse Recovery Fall Time	t_a			27		ns
Reverse Recovery Rise Time	t_b			25		

Notes:

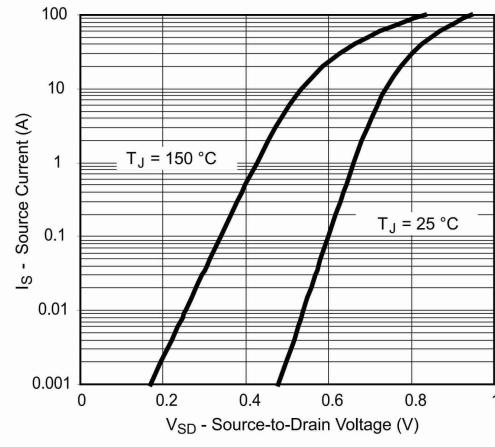
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

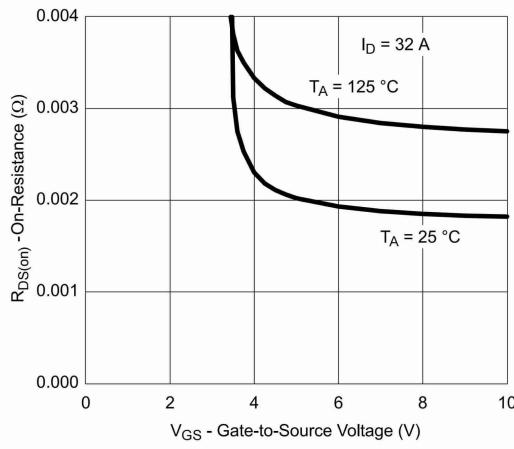
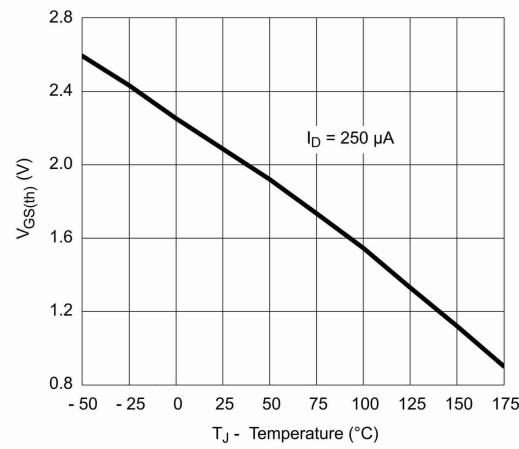
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


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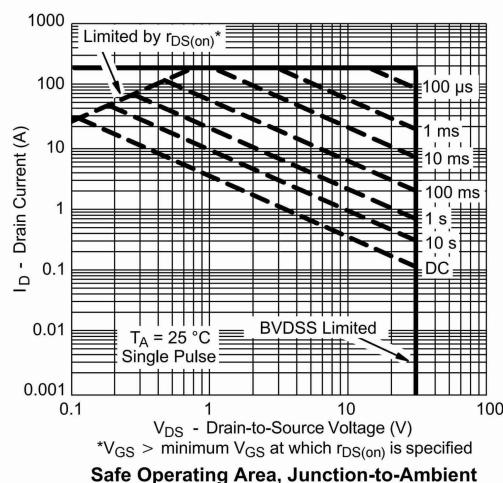
On-Resistance vs. Junction Temperature

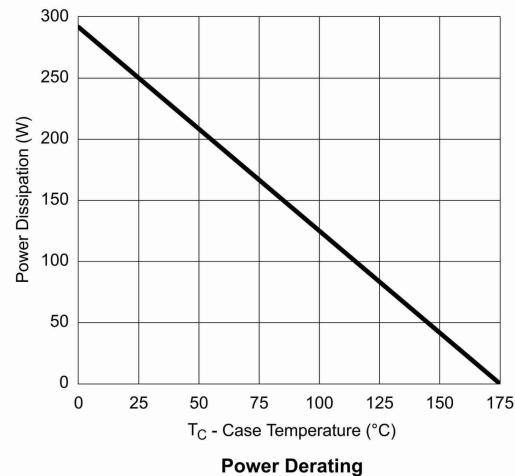
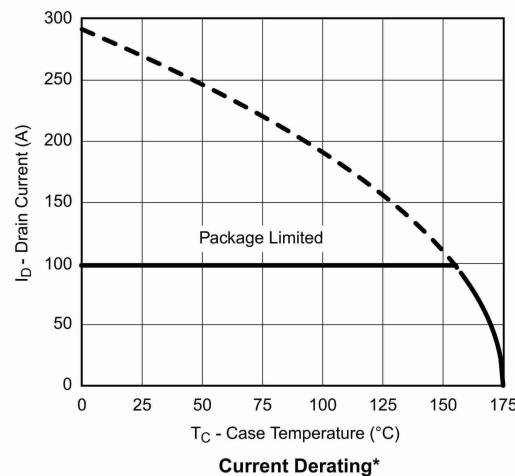


Forward Diode Voltage vs. Temperature

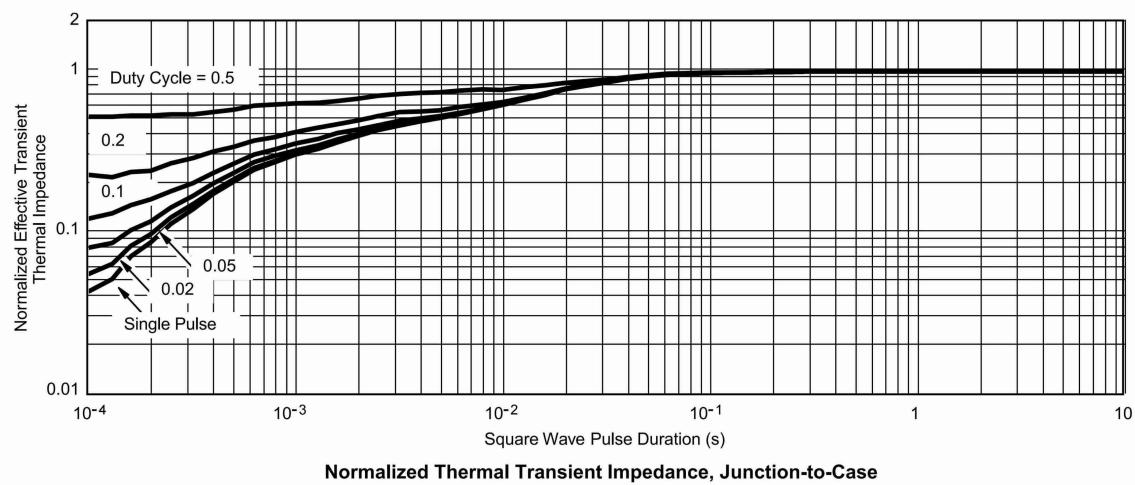
R_{DS(on)} vs. V_{GS} vs. Temperature

Threshold Voltage

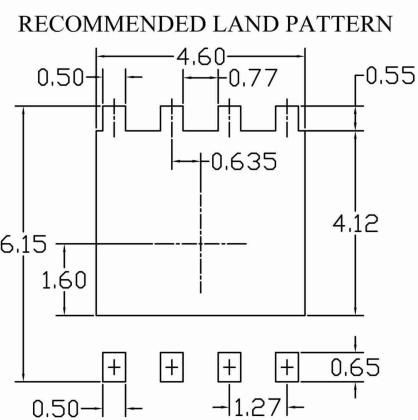
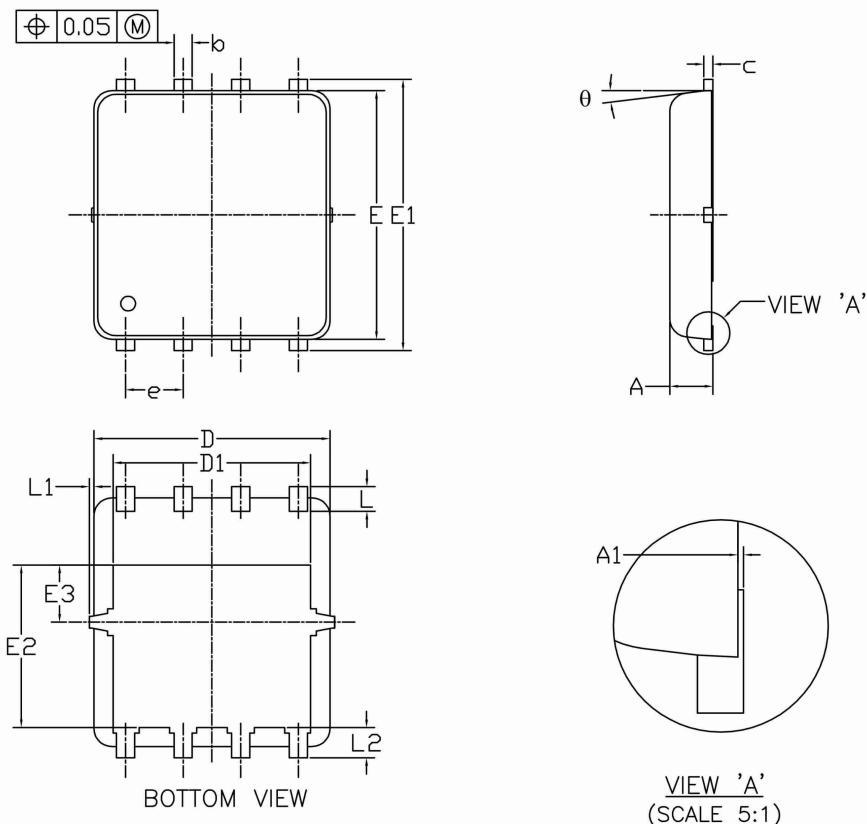


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


* The power dissipation P_D is based on $T_{J(max)} = 175$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



DFN5x6_8L_EP1_P PACKAGE OUTLIN



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	---	0.05	0.000	---	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.10	5.20	5.30	0.201	0.205	0.209
D1	4.25	4.35	4.45	0.167	0.171	0.175
E	5.45	5.55	5.65	0.215	0.219	0.222
E1	5.95	6.05	6.15	0.234	0.238	0.242
E2	3.525	3.625	3.725	0.139	0.143	0.147
E3	1.175	1.275	1.375	0.046	0.050	0.054
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	---	0.15	0	---	0.006
L2	0.68 REF			0.027 REF		
θ	0°	---	10°	0°	---	10°

UNIT: mm

NOTE

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
2. CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

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